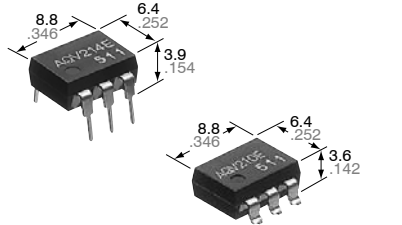


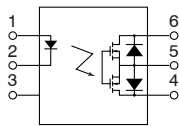
General use and economy type.
DIP (1 Form A) 6-pin type.
Reinforced insulation
5,000V type.

GU-E PhotoMOS

(AQV210E, AQV210EH)



mm inch



FEATURES

- Controls low-level analog signals**
PhotoMOS relays feature extremely low closed-circuit offset voltage to enable control of low-level analog signals without distortion.
- Controlled with low-level input signals**
- Controls various types of loads such as relays, motors, lamps and solenoids.**
- Optical coupling for extremely high isolation**
Unlike mechanical relays, the PhotoMOS relay combines LED and optoelectronic device to transfer signals using light for extremely high isolation.
- Eliminates the need for a counter electromotive force protection diode in the drive circuits on the input side**

- Stable on-resistance**
- Low-level off state leakage current**
- Eliminates the need for a power supply to drive the power MOSFET**
A power supply used to drive the power MOSFET is unnecessary because of the built-in optoelectronic device. This results in easy circuit design and small PC board area.
- Low thermal electromotive force (Approx. 1 μ V)**

TYPICAL APPLICATIONS

- High-speed inspection machines
- Telephone equipment
- Data communication equipment
- Computer

TYPES

Type	I/O isolation	Output rating*		Part No.				Packing quantity	
				Through hole terminal	Surface-mount terminal				
		Load voltage	Load current	Tube packing style		Tape and reel packing style		Tube	Tape and reel
AC/DC	Standard 1,500 V AC	350 V	130 mA	AQV210E	AQV210EA	AQV210EAX	AQV210EAZ		
		400 V	120 mA	AQV214E	AQV214EA	AQV214EAX	AQV214EAZ		
	Reinforced 5,000 V	350 V	130 mA	AQV210EH	AQV210EHA	AQV210EHAX	AQV210EHAZ		
		400 V	120 mA	AQV214EH	AQV214EHA	AQV214EHAX	AQV214EHAZ		

*Indicate the peak AC and DC values.

Note: For space reasons, the SMD terminal shape indicator "A" and the package style indicator "X" or "Z" are not marked on the relay.

RATING

1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

Item		Sym- bol	Type of connec- tion	AQV210E(A)	AQV214E(A)	AQV210EH(A)	AQV214EH(A)	Remarks
Input	LED forward current	I_F		50 mA				
	LED reverse voltage	V_R		5 V				
	Peak forward current	I_{FP}		1 A				$f = 100 \text{ Hz}$, Duty factor = 0.1%
	Power dissipation	P_{in}		75 mW				
Output	Load voltage (peak AC)	V_L		350 V	400 V	350 V	400 V	
	Continuous load current	I_L	A	0.13 A	0.12 A	0.13 A	0.12 A	A connection: Peak AC, DC; B, C connection: DC
			B	0.15 A	0.13 A	0.15 A	0.13 A	
			C	0.17 A	0.15 A	0.17 A	0.15 A	
	Peak load current	I_{peak}		0.4 A	0.3 A	0.4 A	0.3 A	A connection: 100 ms (1 shot), $V_L = DC$
Power dissipation	P_{out}		500 mW					
Total power dissipation		P_T		550 mW				
I/O isolation voltage		V_{iso}		1,500 V AC		5,000 V AC		
Temperature limits	Operating	T_{opr}		-40°C to +85°C -40°F to +185°F				Non-condensing at low temp.
	Storage	T_{stg}		-40°C to +100°C -40°F to +212°F				

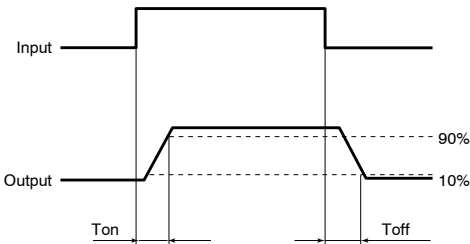
GU-E PhotoMOS (AQV210E, AQV210EH)

2. Electrical characteristics (Ambient temperature: 25°C 77°F)

Item			Symbol	Type of connection	AQV210E(A)	AQV214E(A)	AQV210EH(A)	AQV214EH(A)	Condition	
Input	LED operate current	Typical	I _{Fon}	—	1.1 mA		1.6 mA		I _L = Max.	
		Maximum			3 mA					
	LED turn off current	Minimum	I _{Foff}	—	0.3 mA		0.4 mA		I _L = Max.	
		Typical			1.0 mA		1.5 mA			
LED dropout voltage	Typical	V _F	—	1.25 V (1.14 V at I _F = 5 mA)				I _F = 50 mA		
	Maximum			1.5 V						
Output	On resistance	Typical	R _{on}	A	23 Ω	30 Ω	23 Ω	30 Ω	I _F = 5 mA I _L = Max. Within 1 s on time	
		Maximum			35 Ω	50 Ω	35 Ω	50 Ω		
		Typical	R _{on}	B	11.5 Ω	22.5 Ω	11.5 Ω	22.5 Ω	I _F = 5 mA I _L = Max. Within 1 s on time	
		Maximum			17.5 Ω	25 Ω	17.5 Ω	25 Ω		
	Typical	R _{on}	C	6.0 Ω	11.3 Ω	6.0 Ω	11.3 Ω	I _F = 5 mA I _L = Max. Within 1 s on time		
	Maximum			8.8 Ω	12.5 Ω	8.8 Ω	12.5 Ω			
Output capacitance	Typical	C _{out}	A	45 pF				I _F = 0 mA V _B = 0 V f = 1 MHz		
Off state leakage current	Maximum	—	—	1 μA				I _F = 0 mA V _L = Max.		
Transfer characteristics	Switching speed	Turn on time*	Typical	T _{on}	—	0.5 ms		0.7 ms		I _F = 0 mA, 5 mA** I _L = Max.
			Maximum			2.0 ms				
		Turn off time*	Typical	T _{off}	—	0.05 ms				I _F = 0 mA, 5 mA I _L = Max.
			Maximum			1.0 ms				
	I/O capacitance	Typical	C _{iso}	—	0.8 pF				f = 1 MHz V _B = 0 V	
Maximum	1.5 pF									
Initial I/O isolation resistance	Minimum	R _{iso}	—	1,000 MΩ				500 V DC		

*Turn on/Turn off time

Type of connection



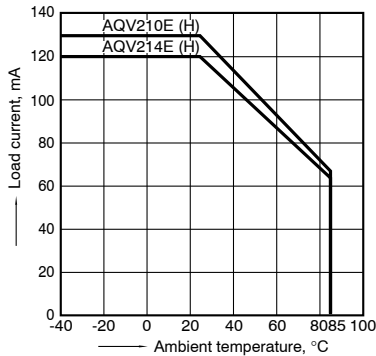
** Recommendable LED forward current
Standard type: I_F = 5 mA
Reinforced type: I_F = 5 to 10 mA

- Dimensions
- Schematic and Wiring Diagrams
- Cautions for Use

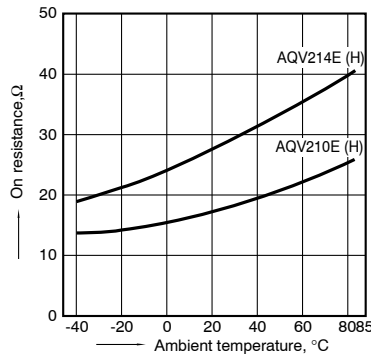
REFERENCE DATA

1. Load current vs. ambient temperature characteristics
Allowable ambient temperature: -40°C to +85°C
-40°F to +185°F

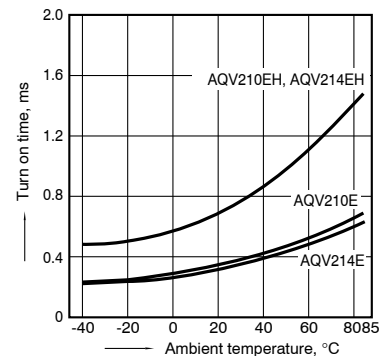
Type of connection: A



2. On-resistance vs. ambient temperature characteristics
Measured portion: between terminals 4 and 6;
LED current: 5 mA; Load voltage: Max. (DC);
Continuous load current: Max. (DC)



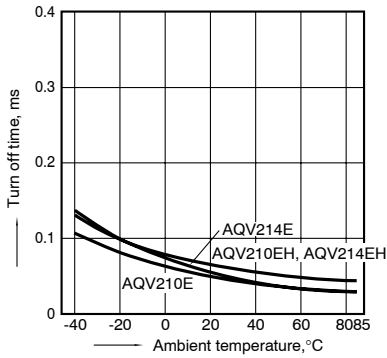
3. Turn on time vs. ambient temperature characteristics
LED current: 5 mA;
Load voltage: Max. (DC);
Continuous load current: Max. (DC)



GU-E PhotoMOS (AQV210E, AQV210EH)

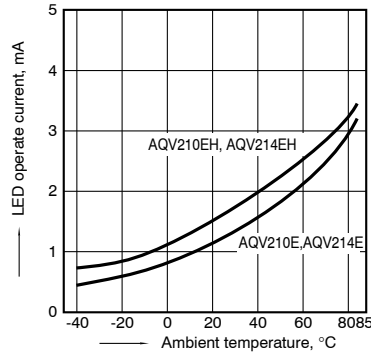
4. Turn off time vs. ambient temperature characteristics

LED current: 5 mA; Load voltage: Max. (DC); Continuous load current: Max. (DC)



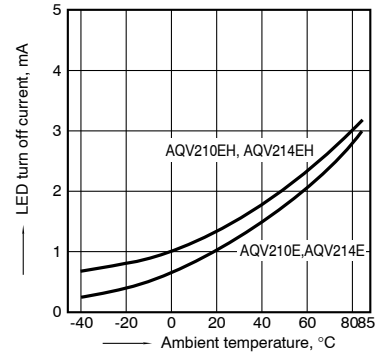
5. LED operate current vs. ambient temperature characteristics

Load voltage: Max. (DC); Continuous load current: Max. (DC)



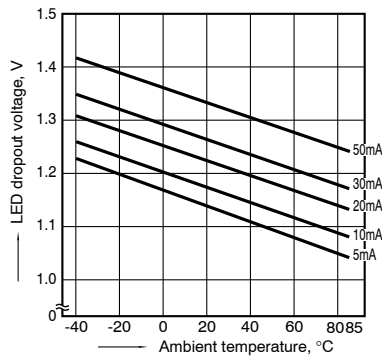
6. LED turn off current vs. ambient temperature characteristics

Load voltage: Max. (DC); Continuous load current: Max. (DC)



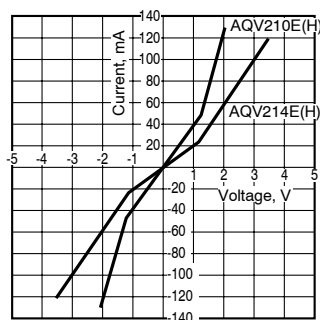
7. LED dropout voltage vs. ambient temperature characteristics

Sample: All types
LED current: 5 to 50 mA



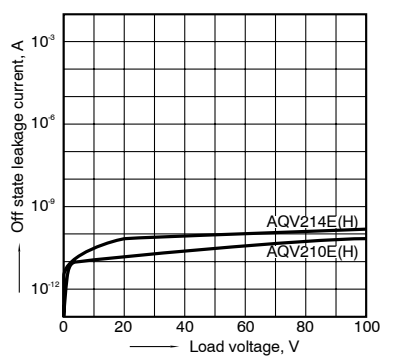
8. Current vs. voltage characteristics of output at MOS portion

Measured portion: between terminals 4 and 6;
Ambient temperature: 25°C 77°F



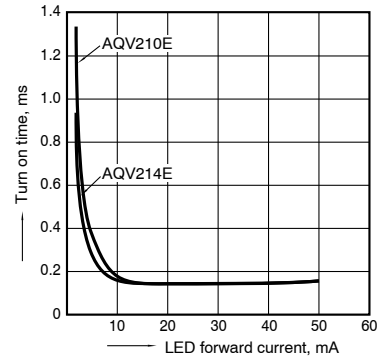
9. Off state leakage current vs. load voltage characteristics

Measured portion: between terminals 4 and 6;
Ambient temperature: 25°C 77°F



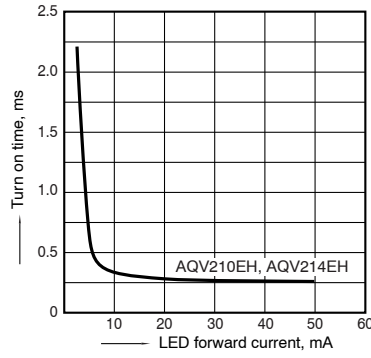
10-(1). Turn on time vs. LED forward current characteristics

Measured portion: between terminals 4 and 6;
Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



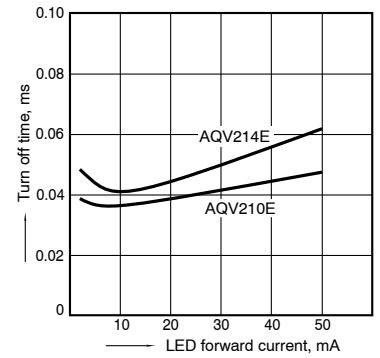
10-(2). Turn on time vs. LED forward current characteristics

Measured portion: between terminals 4 and 6;
Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



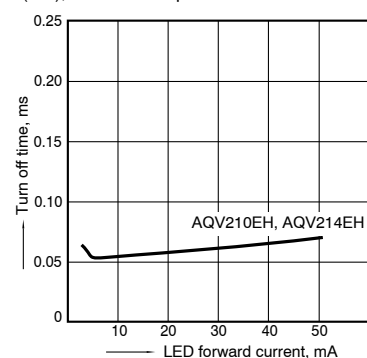
11-(1). Turn off time vs. LED forward current characteristics

Measured portion: between terminals 4 and 6;
Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



11-(2). Turn off time vs. LED forward current characteristics

Measured portion: between terminals 4 and 6;
Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



12. Output capacitance vs. applied voltage characteristics

Measured portion: between terminals 4 and 6;
Frequency: 1 MHz;
Ambient temperature: 25°C 77°F

